

IN THE CLAIMS

Claims 1-10 (Canceled)

11. (Currently amended) A high-frequency power amplifier circuit device, comprising:

a first power transistor which has an input terminal, a first terminal and a second terminal, and which is formed on a semiconductor chip;

a first capacitor having a first terminal coupled to receive a high frequency input signal to be amplified and a second terminal coupled to the input terminal of the first power transistor, ~~wherein~~ so that a high frequency input signal to be amplified is supplied to the input terminal of the first power transistor via the first capacitor; and

a bias circuit which includes a first transistor and a first circuit, the first transistor having an input terminal, a first terminal and a second terminal and being arranged so as to form a current mirror circuit with the first power transistor, and the first circuit receiving a control signal and providing to the first transistor a current signal according to the control signal.

12. (Previously presented) A high-frequency power amplifier circuit device according to claim 11, wherein the first transistor is a field-effect transistor configured as a diode with the input terminal of the first transistor coupled to the first terminal of the first transistor, and wherein the current signal is provided to the first terminal of the first transistor.

13. (Previously presented) A high-frequency power amplifier circuit device according to claim 12, wherein the input terminal of the first power transistor is coupled to the input terminal of the first transistor of the bias circuit.

14. (Previously presented) A high-frequency power amplifier circuit device according to claim 12, wherein the first power transistor is a field-effect transistor.